Erik P A M Bakkers

List of Publications by Year
in descending order

193	18,957	69	134
papers	citations	h-index	g-index
		12330	11939

201	201	201	13541
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Growth of PbTe nanowires by molecular beam epitaxy. Materials for Quantum Technology, 2022, 2, 015001.	3.1	13
2	Electronic Structure and Epitaxy of CdTe Shells on InSb Nanowires. Advanced Science, 2022, 9, e2105722.	11.2	7
3	Supercurrent parity meter in a nanowire Cooper pair transistor. Science Advances, 2022, 8, eabm9896.	10.3	5
4	(Invited) Direct Band Gap Emission from Hexagonal Si-Ge. ECS Meeting Abstracts, 2022, MA2022-01, 1277-1277.	0.0	0
5	Prismatic Ge-rich inclusions in the hexagonal SiGe shell of GaPâ€“Siâ€“SiGe nanowires by controlled faceting. Nanoscale, 2021, 13, 9436-9445.	5.6	1
6	Strong spin-orbit interaction and <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math> -factor renormalization of hole spins in Ge/Si nanowire quantum dots. Physical Review Research, 2021, 3, .	3.6	46
7	Ultrafast hole spin qubit with gate-tunable spinâ€“orbit switch functionality. Nature Nanotechnology, 2021, 16, 308-312.	31.5	97
8	Non-Majorana states yield nearly quantized conductance in proximatized nanowires. Nature Physics, 2021, 17, 482-488.	16.7	105
9	Parity-preserving and magnetic fieldâ€“resilient superconductivity in InSb nanowires with Sn shells. Science, 2021, 372, 508-511.	12.6	50
10	Unveiling Planar Defects in Hexagonal Group IV Materials. Nano Letters, 2021, 21, 3619-3625.	9.1	8
11	Singleâ€Shot Fabrication of Semiconductingâ€“Superconducting Nanowire Devices. Advanced Functional Materials, 2021, 31, 2102388.	14.9	12
12	Full parity phase diagram of a proximitized nanowire island. Physical Review B, 2021, 104, .	3.2	20
13	Universal Platform for Scalable Semiconductorâ€Superconductor Nanowire Networks. Advanced Functional Materials, 2021, 31, 2103062.	14.9	10
14	Shadow-wall lithography of ballistic superconductorâ€“semiconductor quantum devices. Nature Communications, 2021, 12, 4914.	12.8	41
15	Hysteretic magnetoresistance in nanowire devices due to stray fields induced by micromagnets. Nanotechnology, 2021, 32, 095001.	2.6	5
16	Hard Superconducting Gap and Diffusion-Induced Superconductors in Geâ€“Si Nanowires. Nano Letters, 2020, 20, 122-130.	9.1	18
17	Exfoliated hexagonal BN as gate dielectric for InSb nanowire quantum dots with improved gate hysteresis and charge noise. Applied Physics Letters, 2020, 116, 253101.	3.3	4
18	Transmission phase read-out of a large quantum dot in a nanowire interferometer. Nature Communications, 2020, 11, 3666.	12.8	10

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19	Measuring the Optical Absorption of Single Nanowires. Physical Review Applied, 2020, 14, .	3.8	19
20	Probing Lattice Dynamics and Electronic Resonances in Hexagonal Ge and Si_{<i>x</i>}Ge_{1â€“<i>x</i>} Alloys in Nanowires by Raman Spectroscopy. ACS Nano, 2020, 14, 6845-6856.	14.6	17
21	Erasing odd-parity states in semiconductor quantum dots coupled to superconductors. Physical Review B, 2020, 101, .	3.2	10
22	Ballistic Phonons in Ultrathin Nanowires. Nano Letters, 2020, 20, 2703-2709.	9.1	30
23	Kinetic Control of Morphology and Composition in Ge/GeSn Core/Shell Nanowires. ACS Nano, 2020, 14, 2445-2455.	14.6	17
24	Editorial Expression of Concern: Quantized Majorana conductance. Nature, 2020, 581, E4-E4.	27.8	10
25	Direct-bandgap emission from hexagonal Ge and SiGe alloys. Nature, 2020, 580, 205-209.	27.8	231
26	In-plane selective area InSbâ€“Al nanowire quantum networks. Communications Physics, 2020, 3, .	5.3	37
27	Spin Transport in Ferromagnet-InSb Nanowire Quantum Devices. Nano Letters, 2020, 20, 3232-3239.	9.1	24
28	Exploring the Internal Radiative Efficiency of Selective Area Nanowires. Journal of Nanomaterials, 2019, 2019, 1-13.	2.7	0
29	Engineering tunnel junctions on ballistic semiconductor nanowires. Applied Physics Letters, 2019, 115, 043503.	3.3	2
30	Ubiquitous Non-Majorana Zero-Bias Conductance Peaks in Nanowire Devices. Physical Review Letters, 2019, 123, 107703.	7.8	89
31	Strain engineering in Ge/GeSn core/shell nanowires. Applied Physics Letters, 2019, 115, .	3.3	22
32	Phonon Engineering in Twinning Superlattice Nanowires. Nano Letters, 2019, 19, 4702-4711.	9.1	31
33	Spin-Orbit Protection of Induced Superconductivity in Majorana Nanowires. Physical Review Letters, 2019, 122, 187702.	7.8	60
34	High Mobility Stemless InSb Nanowires. Nano Letters, 2019, 19, 3575-3582.	9.1	36
35	Bottom-up grown nanowire quantum devices. MRS Bulletin, 2019, 44, 403-410.	3.5	3
36	Tapered InP nanowire arrays for efficient broadband high-speed single-photon detection. Nature Nanotechnology, 2019, 14, 473-479.	31.5	73

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37	Hexagonal silicon grown from higher order silanes. Nanotechnology, 2019, 30, 295602.	2.6	12
38	Bottomâ€Up Grown 2D InSb Nanostructures. Advanced Materials, 2019, 31, e1808181.	21.0	26
39	Selective-area chemical beam epitaxy of in-plane InAs one-dimensional channels grown on InP(001), InP(111)B, and InP(011) surfaces. Physical Review Materials, 2019, 3, .	2.4	48
40	Multiple Andreev reflections and Shapiro steps in a Ge-Si nanowire Josephson junction. Physical Review Materials, 2019, 3, .	2.4	21
41	Crossed Andreev reflection in InSb flake Josephson junctions. Physical Review Research, 2019, 1, .	3.6	20
42	Split-Channel Ballistic Transport in an InSb Nanowire. Nano Letters, 2018, 18, 2282-2287.	9.1	22
43	Ballistic Majorana nanowire devices. Nature Nanotechnology, 2018, 13, 192-197.	31.5	270
44	Efficient Green Emission from Wurtzite Al_{<i>x</i>}In_{1â€“<i>x</i>}P Nanowires. Nano Letters, 2018, 18, 3543-3549.	9.1	16
45	Majorana zero modes in superconductorâ€“semiconductor heterostructures. Nature Reviews Materials, 2018, 3, 52-68.	48.7	680
46	Critical strain for Sn incorporation into spontaneously graded Ge/GeSn core/shell nanowires. Nanoscale, 2018, 10, 7250-7256.	5.6	28
47	Parity transitions in the superconducting ground state of hybrid InSbâ€“Al Coulomb islands. Nature Communications, 2018, 9, 4801.	12.8	49
48	Electric field tunable superconductor-semiconductor coupling in Majorana nanowires. New Journal of Physics, 2018, 20, 103049.	2.9	81
49	Spinâ€“Orbit Interaction and Induced Superconductivity in a One-Dimensional Hole Gas. Nano Letters, 2018, 18, 6483-6488.	9.1	22
50	Mirage Andreev Spectra Generated by Mesoscopic Leads in Nanowire Quantum Dots. Physical Review Letters, 2018, 121, 127705.	7.8	27
51	Selective-Area Superconductor Epitaxy to Ballistic Semiconductor Nanowires. Nano Letters, 2018, 18, 6121-6128.	9.1	12
52	Fundamentals of the nanowire solar cell: Optimization of the open circuit voltage. Applied Physics Reviews, 2018, 5, 031106.	11.3	71
53	Josephson Effect in a Fewâ€Hole Quantum Dot. Advanced Materials, 2018, 30, e1802257.	21.0	18
54	Twofold origin of strain-induced bending in coreâ€“shell nanowires: the GaP/InGaP case. Nanotechnology, 2018, 29, 315703.	2.6	17

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55	Single, double, and triple quantum dots in Ge/Si nanowires. Applied Physics Letters, 2018, 113, .	3.3	33
56	Charge carrier-selective contacts for nanowire solar cells. Nature Communications, 2018, 9, 3248.	12.8	27
57	Nanowire Arrays as Force Sensors with Superâ€Resolved Localization Position Detection: Application to Optical Measurement of Bacterial Adhesion Forces. Small Methods, 2018, 2, 1700411.	8.6	11
58	Boosting Hole Mobility in Coherently Strained [110]-Oriented Geâ€"Si Coreâ€"Shell Nanowires. Nano Letters, 2017, 17, 2259-2264.	9.1	51
59	Growth and Optical Properties of Direct Band Gap Ge/Ge_{0.87}Sn_{0.13} Core/Shell Nanowire Arrays. Nano Letters, 2017, 17, 1538-1544.	9.1	72
60	Hard Superconducting Gap in InSb Nanowires. Nano Letters, 2017, 17, 2690-2696.	9.1	103
61	Atom-by-Atom Analysis of Semiconductor Nanowires with Parts Per Million Sensitivity. Nano Letters, 2017, 17, 599-605.	9.1	35
62	Single-Crystalline Hexagonal Siliconâ€"Germanium. Nano Letters, 2017, 17, 85-90.	9.1	59
63	Josephson radiation and shot noise of a semiconductor nanowire junction. Physical Review B, 2017, 96, .	3.2	3
64	Experimental phase diagram of zero-bias conductance peaks in superconductor/semiconductor nanowire devices. Science Advances, 2017, 3, e1701476.	10.3	159
65	Effective Surface Passivation of InP Nanowires by Atomic-Layer-Deposited Al₂O₃ with PO_{<i>x</i>} Interlayer. Nano Letters, 2017, 17, 6287-6294.	9.1	68
66	Crystal Phase Quantum Well Emission with Digital Control. Nano Letters, 2017, 17, 6062-6068.	9.1	27
67	Andreev molecules in semiconductor nanowire double quantum dots. Nature Communications, 2017, 8, 585.	12.8	54
68	Conductance through a helical state in an Indium antimonide nanowire. Nature Communications, 2017, 8, 478.	12.8	76
69	Supercurrent Interference in Few-Mode Nanowire Josephson Junctions. Physical Review Letters, 2017, 119, 187704.	7.8	43
70	Ballistic superconductivity in semiconductor nanowires. Nature Communications, 2017, 8, 16025.	12.8	181
71	Optical Emission in Hexagonal SiGe Nanowires. Nano Letters, 2017, 17, 4753-4758.	9.1	51
72	Observation of Conductance Quantization in InSb Nanowire Networks. Nano Letters, 2017, 17, 6511-6515.	9.1	37

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73	InSb Nanowires with Built-In Ga_{<i>x</i>}In_{1â€“<i>x</i>}Sb Tunnel Barriers for Majorana Devices. Nano Letters, 2017, 17, 721-727.	9.1	9
74	Highâ€Efficiency InPâ€Based Photocathode for Hydrogen Production by Interface Energetics Design and Photon Management. Advanced Functional Materials, 2016, 26, 679-686.	14.9	69
75	High-Efficiency Nanowire Solar Cells with Omnidirectionally Enhanced Absorption Due to Self-Aligned Indiumâ€“Tinâ€“Oxide Mie Scatterers. ACS Nano, 2016, 10, 11414-11419.	14.6	150
76	Pseudodirect to Direct Compositional Crossover in Wurtzite GaP/In_{<i>x</i>}Ga_{1â€“<i>x</i>}P Coreâ€“Shell Nanowires. Nano Letters, 2016, 16, 7930-7936.	9.1	19
77	High refractive index in wurtzite GaP measured from Fabry-PÃ©rot resonances. Applied Physics Letters, 2016, 108, .	3.3	5
78	Optical study of the band structure of wurtzite GaP nanowires. Journal of Applied Physics, 2016, 120, .	2.5	34
79	InSb nanowire double quantum dots coupled to a superconducting microwave cavity. Applied Physics Letters, 2016, 108, .	3.3	20
80	Hybrid superconductor-quantum point contact devices using InSb nanowires. Applied Physics Letters, 2016, 109, 233502.	3.3	13
81	Revealing the band structure of InSb nanowires by high-field magnetotransport in the quasiballistic regime. Physical Review B, 2016, 94, .	3.2	3
82	Microwave resonance through the superconducting circuit cavity coupled with InSb double quantum dots. , 2016, , .		0
83	Strong diameter-dependence of nanowire emission coupled to waveguide modes. Applied Physics Letters, 2016, 108, .	3.3	8
84	High-Yield Growth and Characterization of âŸ¨100âŸ© InP pâ€“n Diode Nanowires. Nano Letters, 2016, 16, 3071-3077.	9.1	11
85	Josephson Ï•0-junction in nanowire quantum dots. Nature Physics, 2016, 12, 568-572.	16.7	210
86	Conductance Quantization at Zero Magnetic Field in InSb Nanowires. Nano Letters, 2016, 16, 3482-3486.	9.1	85
87	Optical Properties of Strained Wurtzite Gallium Phosphide Nanowires. Nano Letters, 2016, 16, 3703-3709.	9.1	40
88	Boosting Solar Cell Photovoltage via Nanophotonic Engineering. Nano Letters, 2016, 16, 6467-6471.	9.1	55
89	Impurity and Defect Monitoring in Hexagonal Si and SiGe Nanocrystals. ECS Transactions, 2016, 75, 751-760.	0.5	6
90	Optical transmission matrix as a probe of the photonic strength. Physical Review A, 2016, 94, .	2.5	16

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91	Anisotropic Pauli spin blockade in hole quantum dots. Physical Review B, 2016, 94, .	3.2	33
92	Quantifying losses and thermodynamic limits in nanophotonic solar cells. Nature Nanotechnology, 2016, 11, 1071-1075.	31.5	50
93	Electric-field dependent<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>-factor anisotropy in Ge-Si core-shell nanowire quantum dots. Physical Review B, 2016, 93, .	3.2	48
94	Influence of growth conditions on the performance of InP nanowire solar cells. Nanotechnology, 2016, 27, 454003.	2.6	10
95	Highly tuneable hole quantum dots in Ge-Si core-shell nanowires. Applied Physics Letters, 2016, 109, .	3.3	20
96	Nanowire Arrays as Cell Force Sensors To Investigate Adhesin-Enhanced Holdfast of Single Cell Bacteria and Biofilm Stability. Nano Letters, 2016, 16, 4656-4664.	9.1	65
97	Realization of Microwave Quantum Circuits Using Hybrid Superconducting-Semiconducting Nanowire Josephson Elements. Physical Review Letters, 2015, 115, 127002.	7.8	185
98	Hybrid IIIâ€“V/Silicon Nanowires. Semiconductors and Semimetals, 2015, 93, 231-248.	0.7	1
99	Spin-orbit interaction in InSb nanowires. Physical Review B, 2015, 91, .	3.2	125
100	Directional and Polarized Emission from Nanowire Arrays. Nano Letters, 2015, 15, 4557-4563.	9.1	74
101	Towards high mobility InSb nanowire devices. Nanotechnology, 2015, 26, 215202.	2.6	85
102	Diameter dependence of the thermal conductivity of InAs nanowires. Nanotechnology, 2015, 26, 385401.	2.6	45
103	Hexagonal Silicon Realized. Nano Letters, 2015, 15, 5855-5860.	9.1	142
104	Efficient water reduction with gallium phosphide nanowires. Nature Communications, 2015, 6, 7824.	12.8	123
105	Cracking the Si Shell Growth in Hexagonal GaP-Si Coreâ€“Shell Nanowires. Nano Letters, 2015, 15, 2974-2979.	9.1	23
106	Exploring Crystal Phase Switching in GaP Nanowires. Nano Letters, 2015, 15, 8062-8069.	9.1	55
107	Rational Design: Rationally Designed Singleâ€Crystalline Nanowire Networks (Adv. Mater. 28/2014). Advanced Materials, 2014, 26, 4908-4908.	21.0	1
108	Photoelectrochemical Hydrogen Production on InP Nanowire Arrays with Molybdenum Sulfide Electrocatalysts. Nano Letters, 2014, 14, 3715-3719.	9.1	106

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109	Rationally Designed Singleâ€Crystalline Nanowire Networks. Advanced Materials, 2014, 26, 4875-4879.	21.0	62
110	Nanowire Waveguides Launching Single Photons in a Gaussian Mode for Ideal Fiber Coupling. Nano Letters, 2014, 14, 4102-4106.	9.1	107
111	Reversible Switching of InP Nanowire Growth Direction by Catalyst Engineering. Nano Letters, 2013, 13, 3802-3806.	9.1	107
112	Harnessing nuclear spin polarization fluctuations in a semiconductor nanowire. Nature Physics, 2013, 9, 631-635.	16.7	26
113	Formation and electronic properties of InSb nanocrosses. Nature Nanotechnology, 2013, 8, 859-864.	31.5	115
114	Efficiency Enhancement of InP Nanowire Solar Cells by Surface Cleaning. Nano Letters, 2013, 13, 4113-4117.	9.1	134
115	High optical quality single crystal phase wurtzite and zincblende InP nanowires. Nanotechnology, 2013, 24, 115705.	2.6	59
116	Wurtzite Gallium Phosphide has a direct-band gap. , 2013, , .		2
117	Quantized Conductance in an InSb Nanowire. Nano Letters, 2013, 13, 387-391.	9.1	129
118	Electrical control of single hole spins in nanowire quantum dots. Nature Nanotechnology, 2013, 8, 170-174.	31.5	129
119	Mesoscopic light transport by very strong collective multiple scattering in nanowire mats. Nature Photonics, 2013, 7, 413-418.	31.4	50
120	Direct Band Gap Wurtzite Gallium Phosphide Nanowires. Nano Letters, 2013, 13, 1559-1563.	9.1	262
121	Unit cell structure of the wurtzite phase of GaP nanowires: X-ray diffraction studies and density functional theory calculations. Physical Review B, 2013, 88, .	3.2	28
122	Quantum computing based on semiconductor nanowires. MRS Bulletin, 2013, 38, 809-815.	3.5	46
123	Fast Spin-Orbit Qubit in an Indium Antimonide Nanowire. Physical Review Letters, 2013, 110, 066806.	7.8	142
124	Mesoscopic light trapping in random arrays of semiconductor nanowires. , 2013, , .		0
125	InP nanowire array solar cell with cleaned sidewalls. , 2013, , .		0
126	Spectroscopy of Spin-Orbit Quantum Bits in Indium Antimonide Nanowires. Physical Review Letters, 2012, 108, 166801.	7.8	246

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127	Suppression of Zeeman Gradients by Nuclear Polarization in Double Quantum Dots. Physical Review Letters, 2012, 109, 236805.	7.8	18
128	Growth and optical properties of axial hybrid IIIâ€"V/silicon nanowires. Nature Communications, 2012, 3, 1266.	12.8	105
129	Bright single-photon sources in bottom-up tailored nanowires. Nature Communications, 2012, 3, 737.	12.8	365
130	High yield transfer of ordered nanowire arrays into transparent flexible polymer films. Nanotechnology, 2012, 23, 495305.	2.6	21
131	Position-controlled [100] InP nanowire arrays. Applied Physics Letters, 2012, 100, 053107.	3.3	62
132	Controlling a Nanowire Quantum Dot Band Gap Using a Straining Dielectric Envelope. Nano Letters, 2012, 12, 6206-6211.	9.1	44
133	From InSb Nanowires to Nanocubes: Looking for the Sweet Spot. Nano Letters, 2012, 12, 1794-1798.	9.1	109
134	Spontaneous emission control of single quantum dots in bottom-up nanowire waveguides. Applied Physics Letters, 2012, 100, .	3.3	72
135	Avalanche amplification of a single exciton in a semiconductor nanowire. Nature Photonics, 2012, 6, 455-458.	31.4	95
136	Signatures of Majorana Fermions in Hybrid Superconductor-Semiconductor Nanowire Devices. Science, 2012, 336, 1003-1007.	12.6	3,426
137	Formation of Wurtzite InP Nanowires Explained by Liquid-Ordering. Nano Letters, 2011, 11, 44-48.	9.1	22
138	Electric Field Induced Removal of the Biexciton Binding Energy in a Single Quantum Dot. Nano Letters, 2011, 11, 645-650.	9.1	47
139	Crystal Structure Transfer in Core/Shell Nanowires. Nano Letters, 2011, 11, 1690-1694.	9.1	93
140	The Role of Surface Energies and Chemical Potential during Nanowire Growth. Nano Letters, 2011, 11, 1259-1264.	9.1	92
141	Controlling the Directional Emission of Light by Periodic Arrays of Heterostructured Semiconductor Nanowires. ACS Nano, 2011, 5, 5830-5837.	14.6	23
142	Strong Geometrical Dependence of the Absorption of Light in Arrays of Semiconductor Nanowires. ACS Nano, 2011, 5, 2316-2323.	14.6	169
143	Strong modification of the reflection from birefringent layers of semiconductor nanowires by nanoshells. Applied Physics Letters, 2011, 99, 201108.	3.3	1
144	Ultrafast Dephasing of Light in Strongly Scattering GaP Nanowires. Physical Review Letters, 2011, 106, 143902.	7.8	10

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145	Nanoscale Free-Carrier Profiling of Individual Semiconductor Nanowires by Infrared Near-Field Nanoscopy. Nano Letters, 2010, 10, 1387-1392.	9.1	122
146	Spinâ€“orbit qubit in a semiconductor nanowire. Nature, 2010, 468, 1084-1087.	27.8	588
147	Generic nano-imprint process for fabrication of nanowire arrays. Nanotechnology, 2010, 21, 065305.	2.6	70
148	Surround-gated vertical nanowire quantum dots. Applied Physics Letters, 2010, 96, 233112.	3.3	10
149	Disentangling the effects of spin-orbit and hyperfine interactions on spin blockade. Physical Review B, 2010, 81, .	3.2	97
150	Surface passivated InAs/InP core/shell nanowires. Semiconductor Science and Technology, 2010, 25, 024011.	2.0	92
151	Paired Twins and {112Ì…} Morphology in GaP Nanowires. Nano Letters, 2010, 10, 2349-2356.	9.1	41
152	Single quantum dot nanowire photodetectors. Applied Physics Letters, 2010, 97, .	3.3	41
153	Single Electron Charging in Optically Active Nanowire Quantum Dots. Nano Letters, 2010, 10, 1817-1822.	9.1	46
154	Diameter-dependent conductance of InAs nanowires. Journal of Applied Physics, 2009, 106, .	2.5	77
155	Broadâ€band and Omnidirectional Antireflection Coatings Based on Semiconductor Nanorods. Advanced Materials, 2009, 21, 973-978.	21.0	243
156	Orientationâ€Dependent Opticalâ€Polarization Properties of Single Quantum Dots in Nanowires. Small, 2009, 5, 2134-2138.	10.0	33
157	Selective Excitation and Detection of Spin States in a Single Nanowire Quantum Dot. Nano Letters, 2009, 9, 1989-1993.	9.1	79
158	Large Photonic Strength of Highly Tunable Resonant Nanowire Materials. Nano Letters, 2009, 9, 930-934.	9.1	149
159	Zinc Incorporation via the Vaporâ˘'Liquidâ˘'Solid Mechanism into InP Nanowires. Journal of the American Chemical Society, 2009, 131, 4578-4579.	13.7	41
160	Electric Field Control of Magnetoresistance in InP Nanowires with Ferromagnetic Contacts. Nano Letters, 2009, 9, 2704-2709.	9.1	32
161	Epitaxial Growth of Aligned Semiconductor Nanowire Metamaterials for Photonic Applications. Advanced Functional Materials, 2008, 18, 1039-1046.	14.9	56
162	Inside Front Cover: Epitaxial Growth of Aligned Semiconductor Nanowire Metamaterials for Photonic Applications (Adv. Funct. Mater. 7/2008). Advanced Functional Materials, 2008, 18, 970-970.	14.9	0

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163	Twinning superlattices in indium phosphide nanowires. Nature, 2008, 456, 369-372.	27.8	625
164	Design of Light Scattering in Nanowire Materials for Photovoltaic Applications. Nano Letters, 2008, 8, 2638-2642.	9.1	506
165	Andreev Reflection versus Coulomb Blockade in Hybrid Semiconductor Nanowire Devices. Nano Letters, 2008, 8, 4098-4102.	9.1	45
166	Epitaxial Growth of III-V Nanowires on Group IV Substrates. MRS Bulletin, 2007, 32, 117-122.	3.5	95
167	Modification of the photoluminescence anisotropy of semiconductor nanowires by coupling to surface plasmon polaritons. Optics Letters, 2007, 32, 2097.	3.3	8
168	Scanned Probe Imaging of Quantum Dots inside InAs Nanowires. Nano Letters, 2007, 7, 2559-2562.	9.1	83
169	Three-Dimensional Morphology of GaPâ^'GaAs Nanowires Revealed by Transmission Electron Microscopy Tomography. Nano Letters, 2007, 7, 3051-3055.	9.1	87
170	Electron Emission from Individual Indium Arsenide Semiconductor Nanowires. Nano Letters, 2007, 7, 536-540.	9.1	29
171	Synergetic nanowire growth. Nature Nanotechnology, 2007, 2, 541-544.	31.5	220
172	Remote p-Doping of InAs Nanowires. Nano Letters, 2007, 7, 1144-1148.	9.1	70
173	Single Quantum Dot Nanowire LEDs. Nano Letters, 2007, 7, 367-371.	9.1	349
174	Growth Kinetics of Heterostructured GaPâ^'GaAs Nanowires. Journal of the American Chemical Society, 2006, 128, 1353-1359.	13.7	182
175	Position-controlled epitaxial IIIâ€"V nanowires on silicon. Nanotechnology, 2006, 17, S271-S275.	2.6	116
176	Giant optical birefringence in ensembles of semiconductor nanowires. Applied Physics Letters, 2006, 89, 233117.	3.3	66
177	Supercurrent reversal in quantum dots. Nature, 2006, 442, 667-670.	27.8	375
178	Interface study on heterostructured GaPâ€"GaAs nanowires. Nanotechnology, 2006, 17, 4010-4013.	2.6	60
179	Large redshift in photoluminescence of p-doped InP nanowires induced by Fermi-level pinning. Applied Physics Letters, 2006, 88, 043109.	3.3	67
180	Increase of the Photoluminescence Intensity of InP Nanowires by Photoassisted Surface Passivation. Journal of the American Chemical Society, 2005, 127, 12357-12362.	13.7	95

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181	Tunable Supercurrent Through Semiconductor Nanowires. Science, 2005, 309, 272-275.	12.6	429
182	Epitaxial growth of InP nanowires on germanium. Nature Materials, 2004, 3, 769-773.	27.5	178
183	Synthesis of InP Nanotubes. Journal of the American Chemical Society, 2003, 125, 3440-3441.	13.7	134
184	Single-electron tunneling in InP nanowires. Applied Physics Letters, 2003, 83, 344-346.	3.3	141
185	A tunnelling spectroscopy study on the single-particle energy levels and electron-electron interactions in CdSe quantum dots. Nanotechnology, 2002, 13, 258-262.	2.6	22
186	Shell-Tunneling Spectroscopy of the Single-Particle Energy Levels of Insulating Quantum Dots. Nano Letters, 2001, 1, 551-556.	9.1	119
187	Distance-Dependent Electron Transfer in Au/Spacer/Q-CdSe Assemblies. Angewandte Chemie - International Edition, 2000, 39, 2297-2299.	13.8	71
188	Resonant electron tunneling through semiconducting nanocrystals in a symmetrical and an asymmetrical junction. Physical Review B, 2000, 62, R7743-R7746.	3.2	64
189	Characterization of Photoinduced Electron Tunneling in Gold/SAM/Q-CdSe Systems by Time-Resolved Photoelectrochemistry. Journal of Physical Chemistry B, 2000, 104, 7266-7272.	2.6	79
190	The Rotating Ring-Ring Electrode. Theory and Experiment. Journal of the Electrochemical Society, 2000, 147, 1110.	2.9	8
191	Excited-State Dynamics in CdS Quantum Dots Adsorbed on a Metal Electrode. Journal of Physical Chemistry B, 1999, 103, 2781-2788.	2.6	32
192	Electroless Etching of ZnSe in Aqueous Ferricyanide Solutions: An Electrochemical Study. Journal of the Electrochemical Society, 1997, 144, 2329-2333.	2.9	27
193	Growthâ€Related Formation Mechanism of I3â€Type Basal Stacking Fault in Epitaxially Grown Hexagonal Geâ€2H. Advanced Materials Interfaces, 0, , 2102340.	3.7	0